



MEMC 98-1451/2554.1
PATENT

#5/B
na
6/10/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Robert J. Falster et al.

Art Unit 1775

Serial No. 10/073,506

Filed February 11, 2002

Confirmation No. 6190

For THERMAL ANNEALING PROCESS FOR PRODUCING LOW DEFECT
DENSITY SINGLE CRYSTAL SILICON

Examiner Matthew A. Anderson

May 29, 2003

AMENDMENT B

RECEIVED

JUN 09 2003

TC 1700

TO THE COMMISSIONER FOR PATENTS,

SIR:

Please enter the following amendment, which is submitted in accordance with
the proposed format revisions to 37 CFR 1.121, in response to the Office Action dated
November 29, 2002:

Adjustment date: 06/03/2003 WABDELRI
06/02/2003 WABDELRI-0000093-191345- 10073506
03 FC:1202 36.00 CR -684.00-OP

06/02/2003 WABDELRI 0000093 191345 10073506
01 FC:1253 930.00 OP

06/02/2003 WABDELRI-0000093-191345- 10073506
03 FC:1202 36.00 CH 684.00-OP
06/03/2003 WABDELRI 00000010 10073506
01 FC:1202 684.00 OP